

isc N-Channel MOSFET Transistor

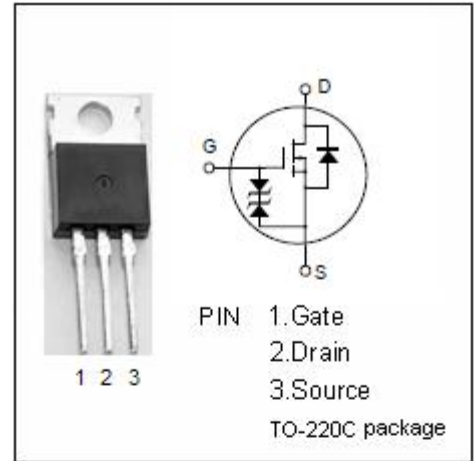
2SK741

DESCRIPTION

- Drain Current  $-I_D=7A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}= 250V(\text{Min})$
- Fast Switching Speed

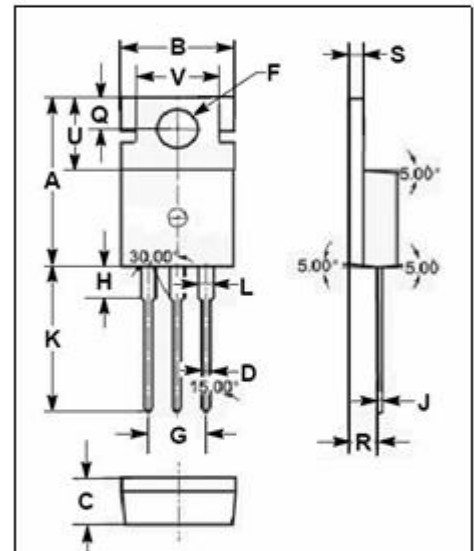
APPLICATIONS

- high speed power switching



ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

| SYMBOL    | PARAMETER                                  | VALUE    | UNIT       |
|-----------|--|----------|------------|
| $V_{DSS}$ | Drain-Source Voltage ( $V_{GS}=0$ )        | 250      | V          |
| $V_{GS}$  | Gate-Source Voltage                        | $\pm 20$ | V          |
| $I_D$     | Drain Current-continuous@ $T_C=25^\circ C$ | 7        | A          |
| $P_{tot}$ | Total Dissipation@ $T_C=25^\circ C$        | 50       | W          |
| $T_j$     | Max. Operating Junction Temperature        | 150      | $^\circ C$ |
| $T_{stg}$ | Storage Temperature Range                  | -55~150  | $^\circ C$ |



| DIM | mm    |       |
|-----|-------|-------|
|     | MIN   | MAX   |
| A   | 15.70 | 15.90 |
| B   | 9.90  | 10.10 |
| C   | 4.20  | 4.40  |
| D   | 0.70  | 0.90  |
| F   | 3.40  | 3.60  |
| G   | 4.98  | 5.18  |
| H   | 2.70  | 2.90  |
| J   | 0.44  | 0.46  |
| K   | 13.20 | 13.40 |
| L   | 1.10  | 1.30  |
| O   | 2.70  | 2.90  |
| R   | 2.50  | 2.70  |
| S   | 1.29  | 1.31  |
| U   | 6.45  | 6.65  |
| V   | 8.66  | 8.86  |

THERMAL CHARACTERISTICS

| SYMBOL       | PARAMETER                              | MAX  | UNIT         |
|--------------|--|------|--------------|
| $R_{th j-c}$ | Thermal Resistance,Junction to Case    | 1.0  | $^\circ C/W$ |
| $R_{th j-a}$ | Thermal Resistance,Junction to Ambient | 62.5 | $^\circ C/W$ |

## isc N-Channel Mosfet Transistor

2SK741

• ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C)

| SYMBOL               | PARAMETER                        | CONDITIONS   | MIN | TYP  | MAX  | UNIT |
|----------------------|----------------------------------|--|-----|------|------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0; I <sub>D</sub> = 10mA                          | 250 |      |      | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage           | V <sub>DS</sub> =10 V <sub>GS</sub> ; I <sub>D</sub> =1mA          | 2.0 |      | 4.0  | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-stage Resistance | V <sub>GS</sub> =10V; I <sub>D</sub> =4A                           |     | 0.40 | 0.55 | Ω    |
| I <sub>GSS</sub>     | Gate Source Leakage Current      | V <sub>GS</sub> = ±16V; V <sub>DS</sub> = 0                        |     |      | ±10  | uA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current  | V <sub>DS</sub> =200V; V <sub>GS</sub> = 0                         |     |      | 250  | uA   |
| V <sub>SD</sub>      | Diode Forward Voltage            | I <sub>F</sub> =7A; V <sub>GS</sub> =0                             |     | 1.2  |      | V    |
| t <sub>r</sub>       | Rise time                        | V <sub>GS</sub> =10V; I <sub>D</sub> =4A;<br>R <sub>L</sub> =7.5 Ω |     | 48   |      | ns   |
| t <sub>on</sub>      | Turn-on time                     |  |     | 60   |      | ns   |
| t <sub>f</sub>       | Fall time                        |  |     | 50   |      | ns   |
| t <sub>off</sub>     | Turn-off time                    |  |     | 120  |      | ns   |